

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 59516-052		SERIAL NO.	
				APPLICANT Zi-Kui LIU, et al.			
				FILING DATE February 24, 2004		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code2 (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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		WO 03/082482 A1	10/09/2003			Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
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INFORMATION DISCLOSURE CITATION IN AN APPLICATION <div style="display: flex; align-items: center; justify-content: center;"> <div style="margin-left: 20px;">(PTO-1449)</div> </div>				ATTY. DOCKET NO. 59516-052		SERIAL NO. 10/784,899	
APPLICANT Zi-Kui LIU, et al.				FILING DATE February 24, 2004		GROUP 1775	
U.S. PATENT DOCUMENTS							
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